

OP27* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

- EVAL-OPAMP-1 Evaluation Board

DOCUMENTATION

Application Notes

- AN-109: High Speed Precision Rectifier
- AN-111: Single-Supply Wien Bridge Oscillator
- AN-112: Single Resistor Controls Wien Bridge Oscillator Frequency
- AN-117: OP-42 Advanced SPICE Macro-Model
- AN-138: SPICE-Compatible Op Amp Macro-Models
- AN-356: User's Guide to Applying and Measuring Operational Amplifier Specifications
- AN-358: Noise and Operational Amplifier Circuits
- AN-649: Using the Analog Devices Active Filter Design Tool
- AN-940: Low Noise Amplifier Selection Guide for Optimal Noise Performance

Data Sheet

- OP27: Military Data Sheet
- OP27: Low Noise, Precision Operational Amplifier Data Sheet

SOFTWARE AND SYSTEMS REQUIREMENTS

- JAN to Generic Cross Reference

TOOLS AND SIMULATIONS

- Analog Filter Wizard
- Analog Photodiode Wizard
- OP27 SPICE Macro-Model

DESIGN RESOURCES

- OP27 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all OP27 EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

Submit feedback for this data sheet.

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10/15—Rev. G to Rev. H

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3/15—Rev. F to Rev. G

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Updated Outline Dimensions	19
Changes to Ordering Guide	21

5/06—Rev. E to Rev. F

Removed References to 745	Universal
Updated 741 to AD741	Universal
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12/05—Rev. D to Rev. E

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9/05—Rev. C to Rev. D

Updated Format.....	Universal
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1/03—Rev. B to Rev. C

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9/01—Rev. 0 to Rev. A

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GENERAL DESCRIPTION

(Continued from Page 1)

PSRR and CMRR exceed 120 dB. These characteristics, coupled with long-term drift of 0.2 $\mu\text{V}/\text{month}$, allow the circuit designer to achieve performance levels previously attained only by discrete designs.

Low cost, high volume production of OP27 is achieved by using an on-chip Zener zap-trimming network. This reliable and stable offset trimming scheme has proven its effectiveness over many years of production history.

The OP27 provides excellent performance in low noise, high accuracy amplification of low level signals. Applications include stable integrators, precision summing amplifiers, precision voltage threshold detectors, comparators, and professional audio circuits such as tape heads and microphone preamplifiers.

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS

$V_S = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 1.

Parameter	Symbol	Test Conditions	OP27A/OP27E			OP27G			Unit
			Min	Typ	Max	Min	Typ	Max	
INPUT OFFSET VOLTAGE ¹	V_{OS}		10	25		30	100		μV
LONG-TERM V_{OS} STABILITY ^{2, 3}	V_{OS}/Time		0.2	1.0		0.4	2.0		$\mu\text{V}/M_0$
INPUT OFFSET CURRENT	I_{OS}		7	35		12	75		nA
INPUT BIAS CURRENT	I_B		± 10	± 40		± 15	± 80		nA
INPUT NOISE VOLTAGE ^{3, 4}	$e_{n\text{ p-p}}$	0.1 Hz to 10 Hz	0.08	0.18		0.09	0.25		$\mu\text{V p-p}$
INPUT NOISE Voltage Density ³	e_n	$f_o = 10\text{ Hz}$	3.5	5.5		3.8	8.0		$\text{nV}/\sqrt{\text{Hz}}$
		$f_o = 30\text{ Hz}$	3.1	4.5		3.3	5.6		$\text{nV}/\sqrt{\text{Hz}}$
		$f_o = 1000\text{ Hz}$	3.0	3.8		3.2	4.5		$\text{nV}/\sqrt{\text{Hz}}$
INPUT NOISE Current Density ³	i_n	$f_o = 10\text{ Hz}$	1.7	4.0		1.7			$\text{pA}/\sqrt{\text{Hz}}$
		$f_o = 30\text{ Hz}$	1.0	2.3		1.0			$\text{pA}/\sqrt{\text{Hz}}$
		$f_o = 1000\text{ Hz}$	0.4	0.6		0.4	0.6		$\text{pA}/\sqrt{\text{Hz}}$
INPUT RESISTANCE Differential Mode ⁵ Common Mode	R_{IN}		1.3	6		0.7	4		$M\Omega$
	R_{INCM}			3			2		$G\Omega$
INPUT VOLTAGE RANGE	IVR		± 11.0	± 12.3		± 11.0	± 12.3		V
COMMON-MODE REJECTION RATIO	CMRR	$V_{CM} = \pm 11\text{ V}$	114	126		100	120		dB
POWER SUPPLY REJECTION RATIO	PSRR	$V_S = \pm 4\text{ V to } \pm 18\text{ V}$	1	10		2	20		$\mu\text{V}/\text{V}$
LARGE SIGNAL VOLTAGE GAIN	A_{VO}	$R_L \geq 2\text{ k}\Omega$, $V_O = \pm 10\text{ V}$	1000	1800		700	1500		V/mV
		$R_L \geq 600\text{ }\Omega$, $V_O = \pm 10\text{ V}$	800	1500		600	1500		V/mV
OUTPUT VOLTAGE SWING	V_O	$R_L \geq 2\text{ k}\Omega$	± 12.0	± 13.8		± 11.5	± 13.5		V
		$R_L \geq 600\text{ }\Omega$	± 10.0	± 11.5		± 10.0	± 11.5		V
SLEW RATE ⁶	SR	$R_L \geq 2\text{ k}\Omega$	1.7	2.8		1.7	2.8		$\text{V}/\mu\text{s}$
GAIN BANDWIDTH PRODUCT ⁶	GBW		5.0	8.0		5.0	8.0		MHz
OPEN-LOOP OUTPUT RESISTANCE	R_O	$V_O = 0$, $I_O = 0$	70			70			Ω
POWER CONSUMPTION	P_d	V_O	90	140		100	170		mW
OFFSET ADJUSTMENT RANGE		$R_P = 10\text{ k}\Omega$	± 4.0			± 4.0			mV

¹ Input offset voltage measurements are performed approximately 0.5 seconds after application of power. A/E grades guaranteed fully warmed up.

² Long-term input offset voltage stability refers to the average trend line of V_{OS} vs. time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in V_{OS} during the first 30 days are typically $2.5\text{ }\mu\text{V}$. Refer to the Typical Performance Characteristics section.

³ Sample tested.

⁴ See voltage noise test circuit (Figure 31).

⁵ Guaranteed by input bias current.

⁶ Guaranteed by design.

$V_S = \pm 15\text{ V}$, $-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Test Conditions	OP27A			Unit
			Min	Typ	Max	
INPUT OFFSET VOLTAGE ¹	V_{OS}			30	60	μV
AVERAGE INPUT OFFSET DRIFT	TCV_{OS}^2					
	TCV_{OSn}^3			0.2	0.6	$\mu\text{V}/^\circ\text{C}$
INPUT OFFSET CURRENT	I_{OS}			15	50	nA
INPUT BIAS CURRENT	I_B			± 20	± 60	nA
INPUT VOLTAGE RANGE	IVR		± 10.3	± 11.5		V
COMMON-MODE REJECTION RATIO	CMRR	$V_{CM} = \pm 10\text{ V}$	108	122		dB
POWER SUPPLY REJECTION RATIO	PSRR	$V_S = \pm 4.5\text{ V to } \pm 18\text{ V}$		2	16	$\mu\text{V/V}$
LARGE SIGNAL VOLTAGE GAIN	A_{VO}	$R_L \geq 2\text{ k}\Omega$, $V_O = \pm 10\text{ V}$	600	1200		V/mV
OUTPUT VOLTAGE SWING	V_O	$R_L \geq 2\text{ k}\Omega$	± 11.5	± 13.5		V

¹ Input offset voltage measurements are performed by automated test equipment approximately 0.5 seconds after application of power. A/E grades guaranteed fully warmed up.

² The TCV_{OS} performance is within the specifications unnull or when nulled with $R_P = 8\text{ k}\Omega$ to $20\text{ k}\Omega$. TCV_{OS} is 100% tested for A/E grades, sample tested for G grades.

³ Guaranteed by design.

$V_S = \pm 15\text{ V}$, $-25^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$ for OP27J and OP27Z and $-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$ for OP27GS, unless otherwise noted.

Table 3.

Parameter	Symbol	Test Conditions	OP27E			OP27G			Unit
			Min	Typ	Max	Min	Typ	Max	
INPUT ONSET VOLTAGE	V_{OS}		20	50		55	220		μV
AVERAGE INPUT OFFSET DRIFT	TCV_{OS}^1		0.2	0.6		0.4	1.8		$\mu\text{V}/^\circ\text{C}$
	TCV_{OSn}^2		0.2	0.6		0.4	1.8		$\mu\text{V}/^\circ\text{C}$
INPUT OFFSET CURRENT	I_{OS}		10	50		20	135		nA
INPUT BIAS CURRENT	I_B		± 14	± 60		± 25	± 150		nA
INPUT VOLTAGE RANGE	IVR		± 10.5	± 11.8		± 10.5	± 11.8		V
COMMON-MODE REJECTION RATIO	CMRR	$V_{CM} = \pm 10\text{ V}$	110	124		96	118		dB
POWER SUPPLY REJECTION RATIO	PSRR	$V_S = \pm 4.5\text{ V to } \pm 18\text{ V}$		2	15		2	32	$\mu\text{V/V}$
LARGE SIGNAL VOLTAGE GAIN	A_{VO}	$R_L \geq 2\text{ k}\Omega$, $V_O = \pm 10\text{ V}$	750	1500		450	1000		V/mV
OUTPUT VOLTAGE SWING	V_O	$R_L \geq 2\text{ k}\Omega$	± 11.7	± 13.6		± 11.0	± 13.3		V

¹ The TCV_{OS} performance is within the specifications unnull or when nulled with $R_P = 8\text{ k}\Omega$ to $20\text{ k}\Omega$. TCV_{OS} is 100% tested for A/E grades, sample tested for C/G grades.

² Guaranteed by design.

TYPICAL ELECTRICAL CHARACTERISTICS

$V_S = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$ unless otherwise noted.

Table 4.

Parameter	Symbol	Test Conditions	OP27N Typical	Unit
AVERAGE INPUT OFFSET VOLTAGE DRIFT ¹	TCV_{OS} or TCV_{OSn}	Nullled or unnullled, $R_P = 8\text{ k}\Omega$ to $20\text{ k}\Omega$	0.2	$\mu\text{V}/^\circ\text{C}$
AVERAGE INPUT OFFSET CURRENT DRIFT	TCI_{OS}		80	$\text{pA}/^\circ\text{C}$
AVERAGE INPUT BIAS CURRENT DRIFT	TCI_B		100	$\text{pA}/^\circ\text{C}$
INPUT NOISE VOLTAGE DENSITY	e_n	$f_O = 10\text{ Hz}$	3.5	$\text{nV}/\sqrt{\text{Hz}}$
		$f_O = 30\text{ Hz}$	3.1	$\text{nV}/\sqrt{\text{Hz}}$
		$f_O = 1000\text{ Hz}$	3.0	$\text{nV}/\sqrt{\text{Hz}}$
INPUT NOISE CURRENT DENSITY	i_n	$f_O = 10\text{ Hz}$	1.7	$\text{pA}/\sqrt{\text{Hz}}$
		$f_O = 30\text{ Hz}$	1.0	$\text{pA}/\sqrt{\text{Hz}}$
		$f_O = 1000\text{ Hz}$	0.4	$\text{pA}/\sqrt{\text{Hz}}$
INPUT NOISE VOLTAGE SLEW RATE	e_{np-p}	0.1 Hz to 10 Hz	0.08	$\mu\text{V p-p}$
	SR	$R_L \geq 2\text{ k}\Omega$	2.8	$\text{V}/\mu\text{s}$
GAIN BANDWIDTH PRODUCT	GBW		8	MHz

¹ Input offset voltage measurements are performed by automated test equipment approximately 0.5 seconds after application of power.

ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter	Rating
Supply Voltage	± 22 V
Input Voltage ¹	± 22 V
Output Short-Circuit Duration	Indefinite
Differential Input Voltage ²	± 0.7 V
Differential Input Current ²	± 25 mA
Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
Operating Temperature Range	
OP27A (J, Z)	-55°C to $+125^{\circ}\text{C}$
OP27E (Z)	-25°C to $+85^{\circ}\text{C}$
OP27E (P)	0°C to 70°C
OP27G (P, S, J, Z)	-40°C to $+85^{\circ}\text{C}$
Lead Temperature Range (Soldering, 60 sec)	300°C
Junction Temperature	-65°C to $+150^{\circ}\text{C}$

¹ For supply voltages less than ± 22 V, the absolute maximum input voltage is equal to the supply voltage.

² The inputs of the OP27 are protected by back-to-back diodes. Current limiting resistors are not used in order to achieve low noise. If differential input voltage exceeds ± 0.7 V, the input current should be limited to 25 mA.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions, that is, θ_{JA} is specified for device in socket for TO-99, CERDIP, and PDIP packages; θ_{JA} is specified for device soldered to printed circuit board for SOIC package.

Absolute maximum ratings apply to both dice and packaged parts, unless otherwise noted.

Table 6.

Package Type	θ_{JA}	θ_{JC}	Unit
8-Lead Metal Can (TO-99) (J)	150	18	$^{\circ}\text{C}/\text{W}$
8-Lead CERDIP (Z)	148	16	$^{\circ}\text{C}/\text{W}$
8-Lead PDIP (P)	103	43	$^{\circ}\text{C}/\text{W}$
8-Lead SOIC_N (S)	158	43	$^{\circ}\text{C}/\text{W}$

ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

TYPICAL PERFORMANCE CHARACTERISTICS

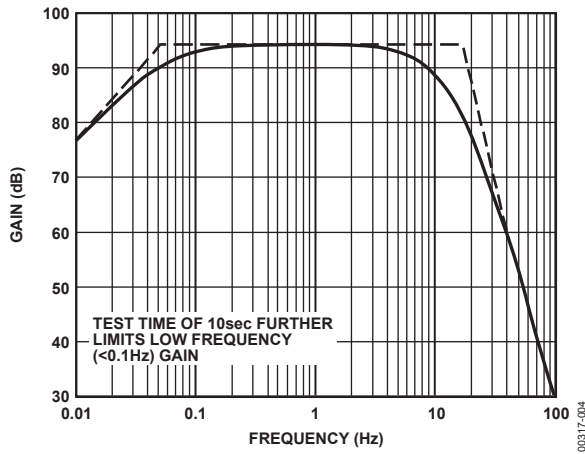


Figure 4. 0.1 Hz to 10 Hz p-p Noise Tester Frequency Response

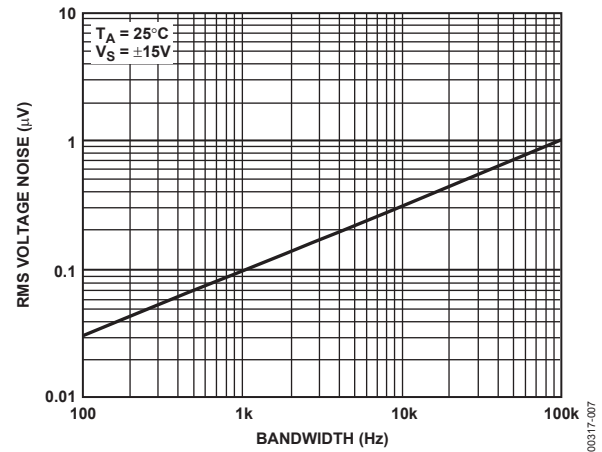


Figure 7. Input Wideband Voltage Noise vs. Bandwidth (0.1 Hz to Frequency Indicated)

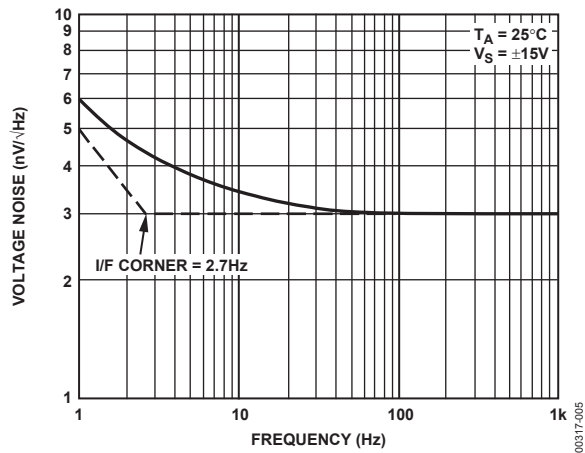


Figure 5. Voltage Noise Density vs. Frequency

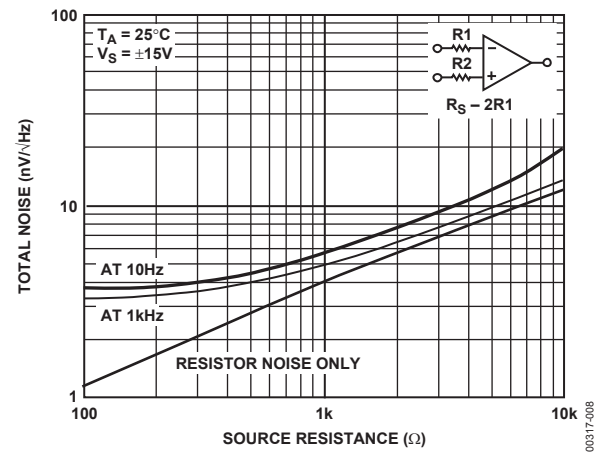


Figure 8. Total Noise vs. Sourced Resistance

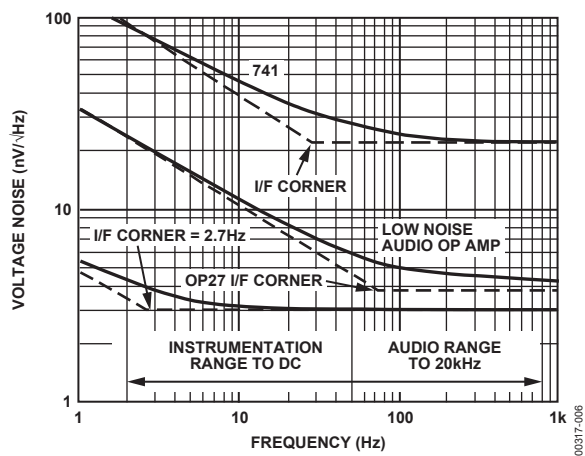


Figure 6. A Comparison of Op Amp Voltage Noise Spectra

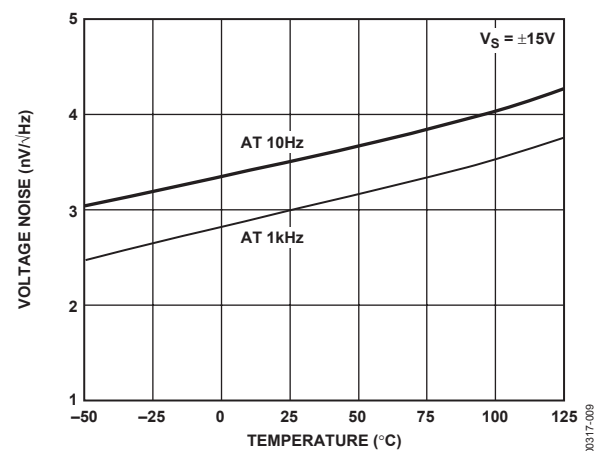


Figure 9. Voltage Noise Density vs. Temperature

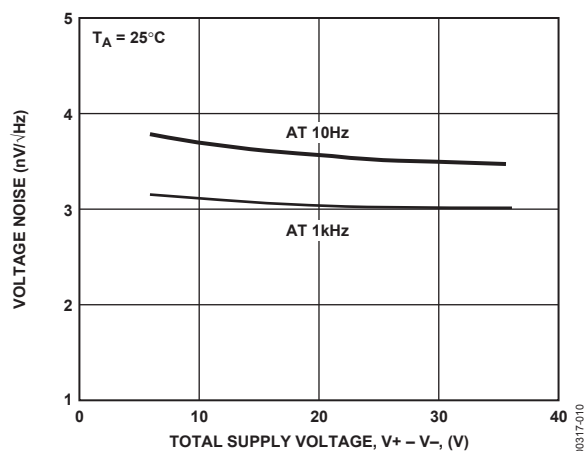


Figure 10. Voltage Noise Density vs. Supply Voltage

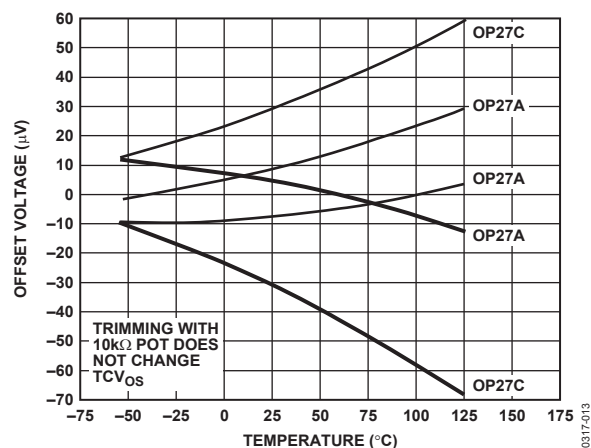


Figure 13. Offset Voltage Drift of Five Representative Units vs. Temperature

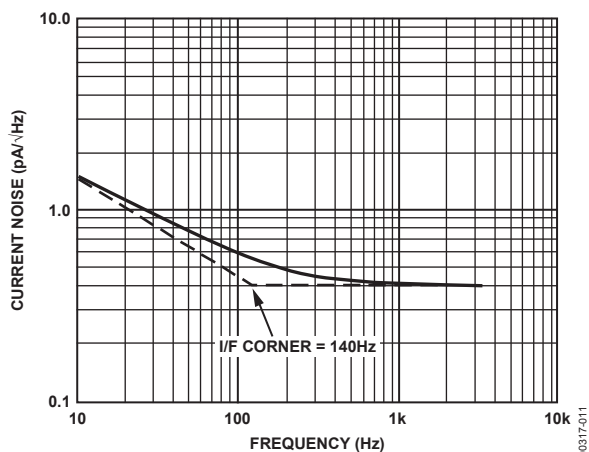


Figure 11. Current Noise Density vs. Frequency

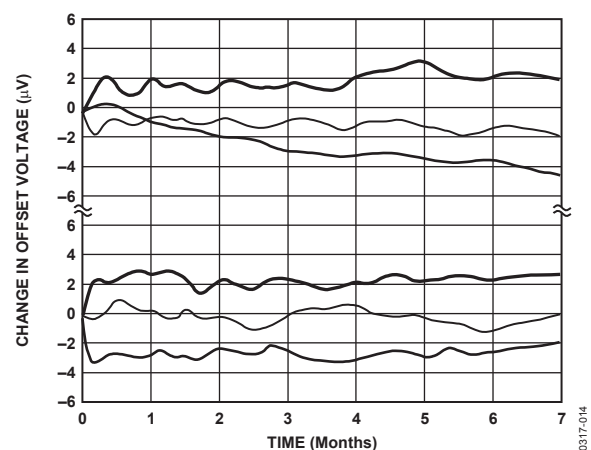


Figure 14. Long-Term Offset Voltage Drift of Six Representative Units

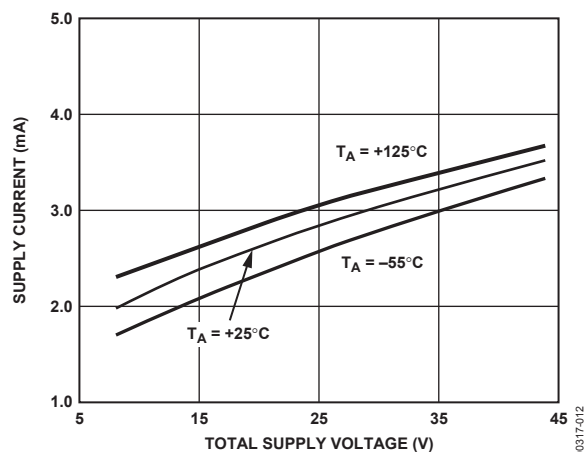


Figure 12. Supply Current vs. Supply Voltage

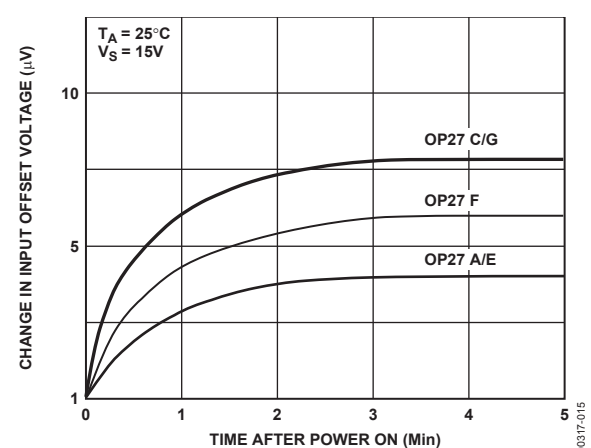


Figure 15. Warm-Up Offset Voltage Drift

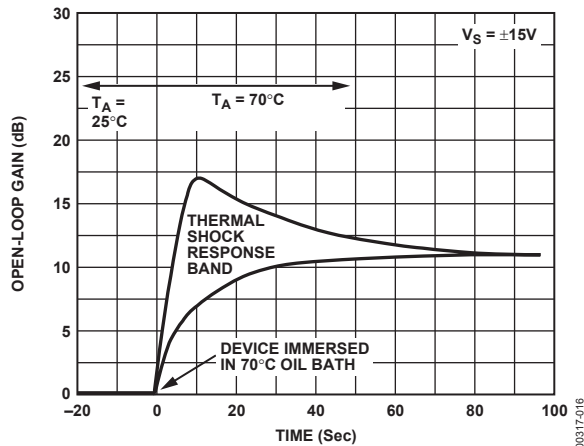


Figure 16. Offset Voltage Change Due to Thermal Shock

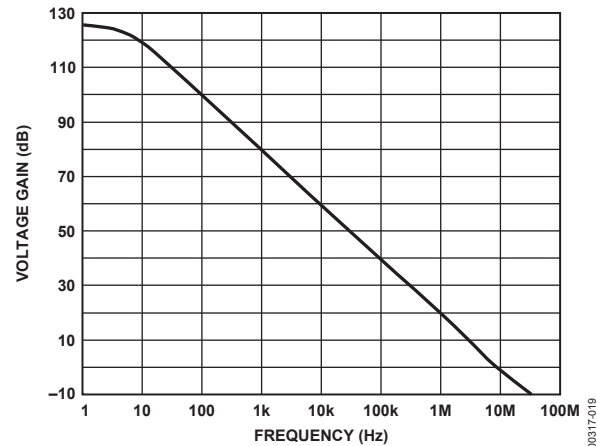


Figure 19. Open-Loop Gain vs. Frequency

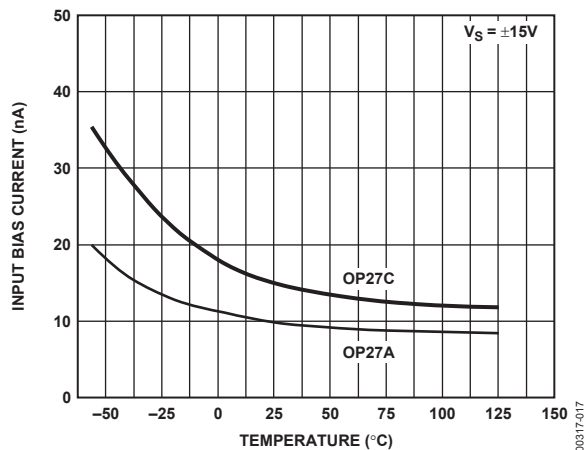


Figure 17. Input Bias Current vs. Temperature

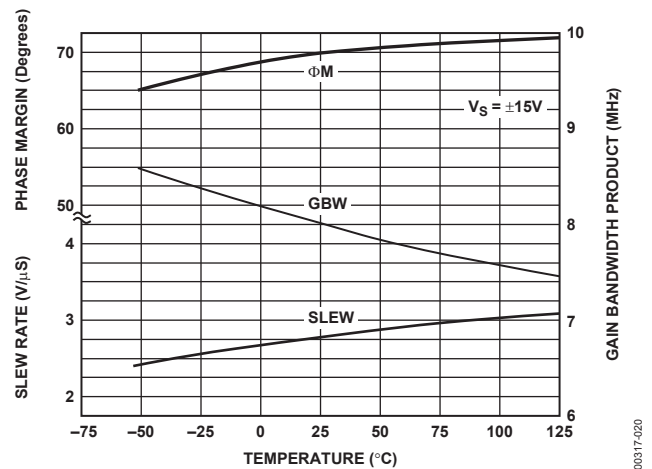


Figure 20. Slew Rate, Gain Bandwidth Product, Phase Margin vs. Temperature

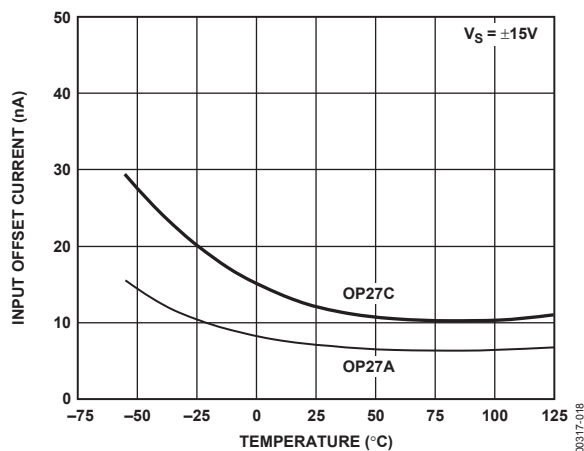


Figure 18. Input Offset Current vs. Temperature

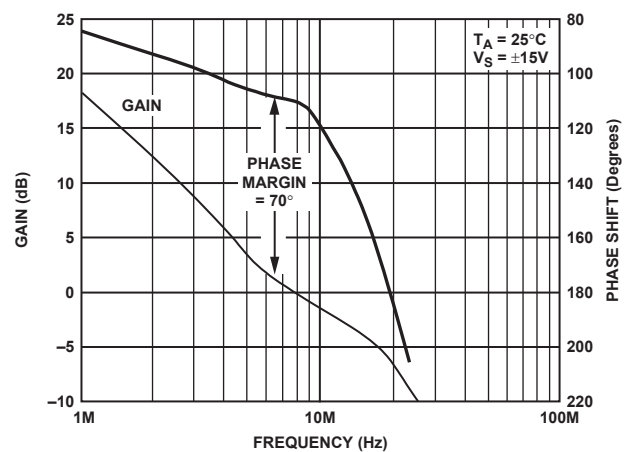


Figure 21. Gain, Phase Shift vs. Frequency

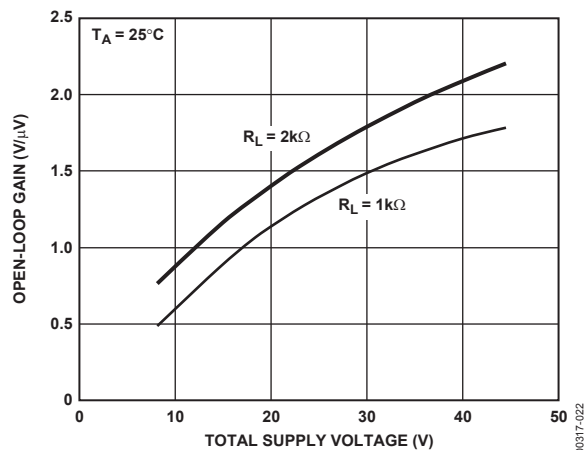


Figure 22. Open-Loop Voltage Gain vs. Supply Voltage

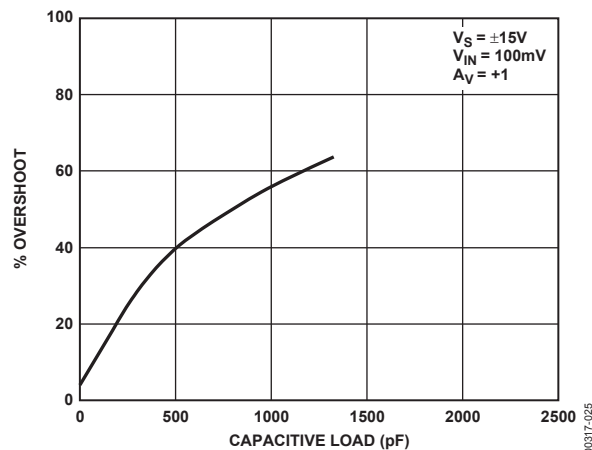


Figure 25. Small-Signal Overshoot vs. Capacitive Load

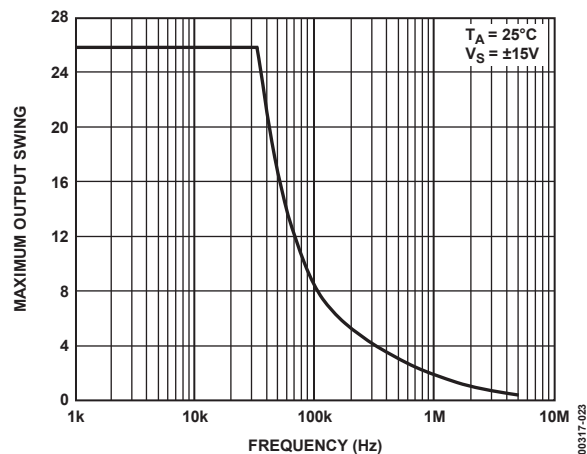


Figure 23. Maximum Output Swing vs. Frequency

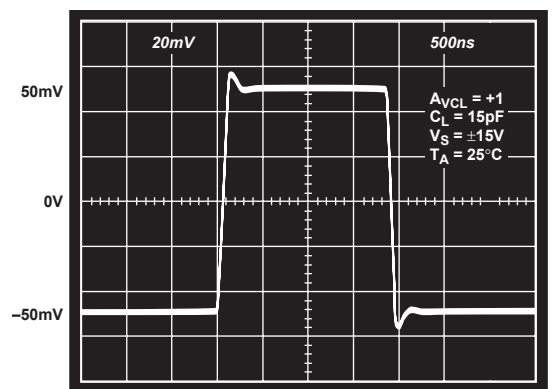


Figure 26. Small-Signal Transient Response

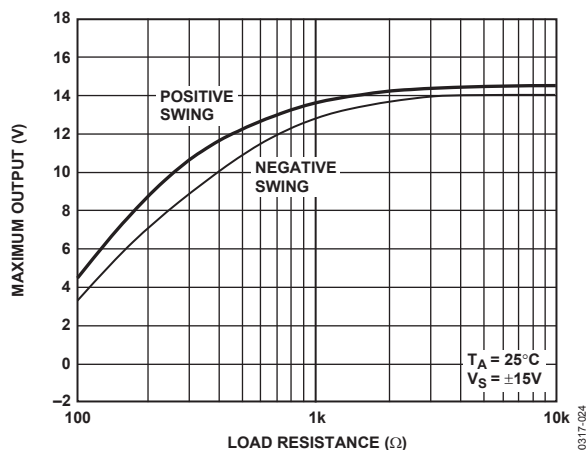


Figure 24. Maximum Output Voltage vs. Load Resistance

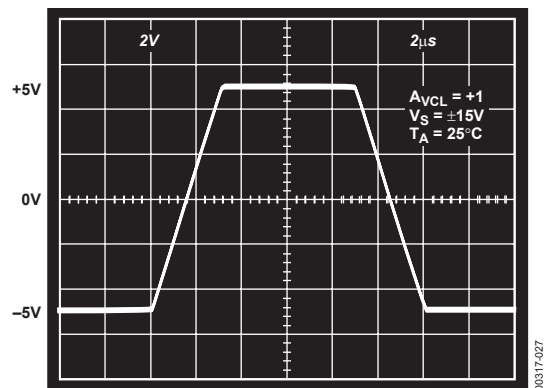


Figure 27. Large Signal Transient Response

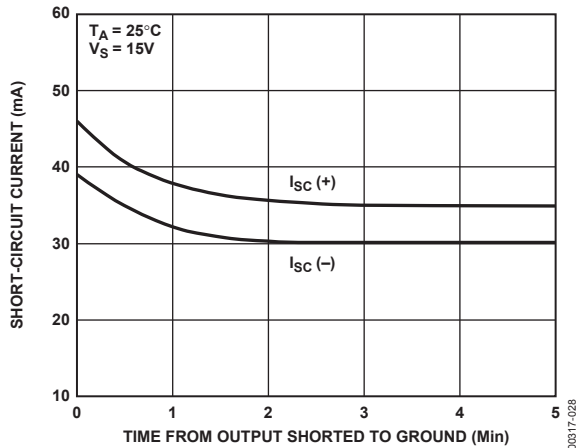


Figure 28. Short-Circuit Current vs. Time

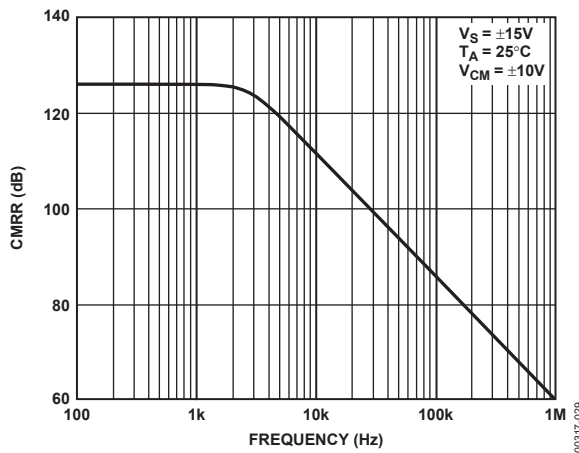


Figure 29. CMRR vs. Frequency

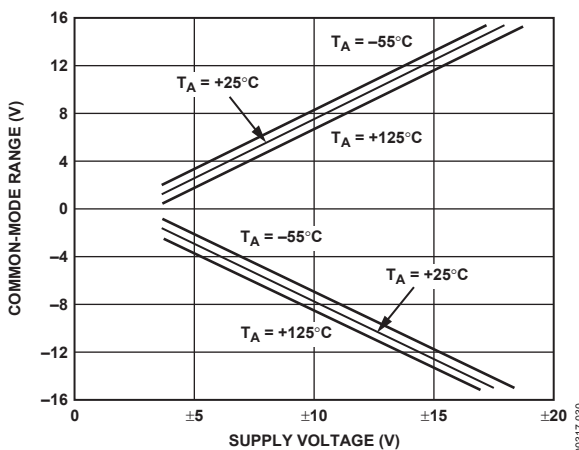


Figure 30. Common-Mode Input Range vs. Supply Voltage

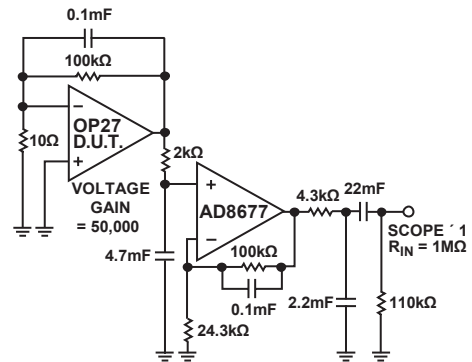


Figure 31. Voltage Noise Test Circuit (0.1 Hz to 10 Hz)

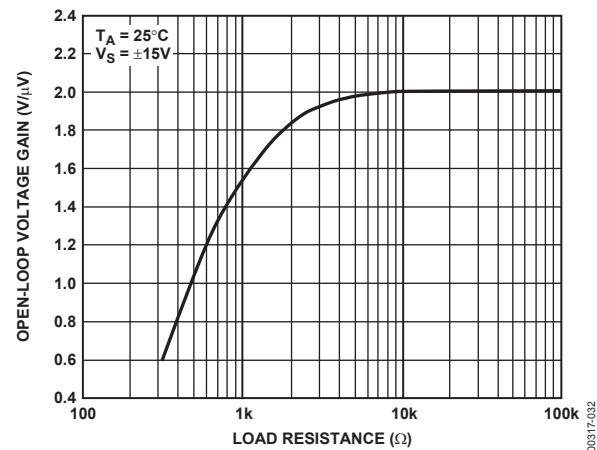


Figure 32. Open-Loop Voltage Gain vs. Load Resistance

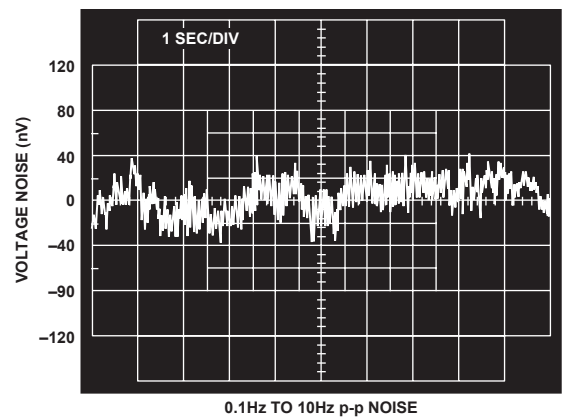


Figure 33. Low Frequency Noise

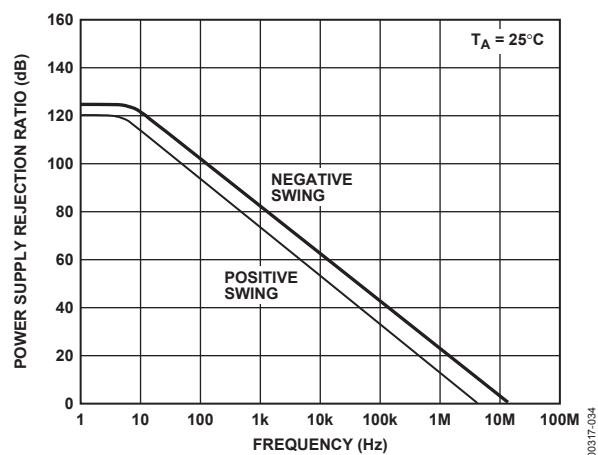


Figure 34. PSRR vs. Frequency

APPLICATIONS INFORMATION

OP27 series units can be inserted directly into OP07 sockets with or without removal of external compensation or nulling components. OP27 offset voltage can be nulled to 0 (or another desired setting) using a potentiometer (see Figure 35).

The OP27 provides stable operation with load capacitances of up to 2000 pF and ± 10 V swings; larger capacitances should be decoupled with a 50 Ω resistor inside the feedback loop. The OP27 is unity-gain stable.

Thermoelectric voltages generated by dissimilar metals at the input terminal contacts can degrade the drift performance. Best operation is obtained when both input contacts are maintained at the same temperature.

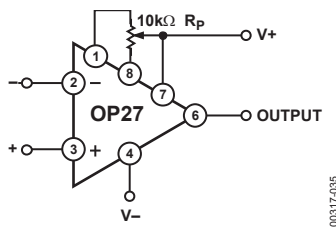


Figure 35. Offset Nulling Circuit

OFFSET VOLTAGE ADJUSTMENT

The input offset voltage of the OP27 is trimmed at wafer level. However, if further adjustment of V_{OS} is necessary, a 10 k Ω trim potentiometer can be used. TCV_{OS} is not degraded (see Figure 35). Other potentiometer values from 1 k Ω to 1 M Ω can be used with a slight degradation (0.1 $\mu\text{V}/^\circ\text{C}$ to 0.2 $\mu\text{V}/^\circ\text{C}$) of TCV_{OS} . Trimming to a value other than zero creates a drift of approximately $(V_{OS}/300)$ $\mu\text{V}/^\circ\text{C}$. For example, the change in TCV_{OS} is 0.33 $\mu\text{V}/^\circ\text{C}$ if V_{OS} is adjusted to 100 μV . The offset voltage adjustment range with a 10 k Ω potentiometer is ± 4 mV. If smaller adjustment range is required, the nulling sensitivity can be reduced by using a smaller potentiometer in conjunction with fixed resistors. For example, Figure 36 shows a network that has a ± 280 μV adjustment range.

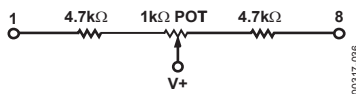


Figure 36. Offset Voltage Adjustment

NOISE MEASUREMENTS

To measure the 80 nV p-p noise specification of the OP27 in the 0.1 Hz to 10 Hz range, the following precautions must be observed:

- The device must be warmed up for at least five minutes. As shown in the warm-up drift curve, the offset voltage typically changes 4 μV due to increasing chip temperature after power-up. In the 10-second measurement interval, these temperature-induced effects can exceed tens-of-nanovolts.
- For similar reasons, the device has to be well-shielded from air currents. Shielding minimizes thermocouple effects.
- Sudden motion in the vicinity of the device can also feedthrough to increase the observed noise.
- The test time to measure 0.1 Hz to 10 Hz noise should not exceed 10 seconds. As shown in the noise-tester frequency response curve, the 0.1 Hz corner is defined by only one zero. The test time of 10 seconds acts as an additional zero to eliminate noise contributions from the frequency band below 0.1 Hz.
- A noise voltage density test is recommended when measuring noise on a large number of units. A 10 Hz noise voltage density measurement correlates well with a 0.1 Hz to 10 Hz p-p noise reading, since both results are determined by the white noise and the location of the 1/f corner frequency.

UNITY-GAIN BUFFER APPLICATIONS

When $R_f \leq 100$ Ω and the input is driven with a fast, large signal pulse (> 1 V), the output waveform looks as shown in the pulsed operation diagram (see Figure 37).

During the fast feedthrough-like portion of the output, the input protection diodes effectively short the output to the input, and a current, limited only by the output short-circuit protection, is drawn by the signal generator. With $R_f \geq 500$ Ω , the output is capable of handling the current requirements ($I_L \leq 20$ mA at 10 V); the amplifier stays in its active mode and a smooth transition occurs.

When $R_f > 2$ k Ω , a pole is created with R_f and the amplifier's input capacitance (8 pF) that creates additional phase shift and reduces phase margin. A small capacitor (20 pF to 50 pF) in parallel with R_f eliminates this problem.

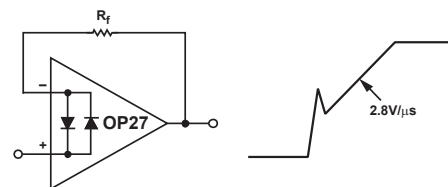


Figure 37. Pulsed Operation

COMMENTS ON NOISE

The **OP27** is a very low noise, monolithic op amp. The outstanding input voltage noise characteristics of the **OP27** are achieved mainly by operating the input stage at a high quiescent current. The input bias and offset currents, which would normally increase, are held to reasonable values by the input bias current cancellation circuit. The **OP27A/OP27E** has I_B and I_{OS} of only ± 40 nA and 35 nA at 25°C respectively. This is particularly important when the input has a high source resistance. In addition, many audio amplifier designers prefer to use direct coupling. The high I_B , V_{OS} , and TCV_{OS} of previous designs have made direct coupling difficult, if not impossible, to use.

Voltage noise is inversely proportional to the square root of bias current, but current noise is proportional to the square root of bias current. The noise advantage of the **OP27** disappears when high source resistors are used. Figure 38, Figure 39, Figure 40 compare the observed total noise of the **OP27** with the noise performance of other devices in different circuit applications.

$$\text{Total Noise} = \left[\frac{(\text{Voltage Noise})^2 + (\text{Current Noise} \times R_s)^2 + (\text{Resistor Noise})^2}{\text{}} \right]^{1/2}$$

Figure 38 shows noise vs. source resistance at 1000 Hz. The same plot applies to wideband noise. To use this plot, multiply the vertical scale by the square root of the bandwidth.

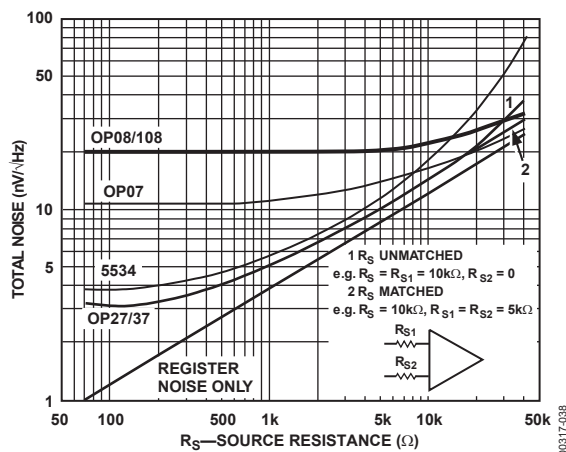


Figure 38. Noise vs. Source Resistance (Including Resistor Noise) at 1000 Hz

At $R_s < 1$ k Ω , the low voltage noise of the **OP27** is maintained. With $R_s < 1$ k Ω , total noise increases but is dominated by the resistor noise rather than current or voltage noise. It is only beyond R_s of 20 k Ω that current noise starts to dominate. The argument can be made that current noise is not important for applications with low-to-moderate source resistances. The crossover between the **OP27** and **OP07** noise occurs in the 15 k Ω to 40 k Ω region.

Figure 39 shows the 0.1 Hz to 10 Hz p-p noise. Here the picture is less favorable; resistor noise is negligible and current noise becomes important because it is inversely proportional to the square root of frequency. The crossover with the **OP07** occurs in the 3 k Ω to 5 k Ω range depending on whether balanced or unbalanced source resistors are used (at 3 k Ω the I_B and I_{OS} error also can be $3\times$ the V_{OS} spec).

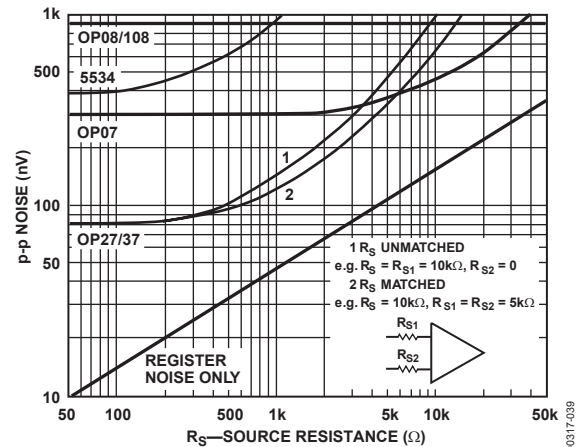


Figure 39. Peak-to-Peak Noise (0.1 Hz to 10 Hz) as Source Resistance (Includes Resistor Noise)

For low frequency applications, the **OP07** is better than the **OP27/OP37** when $R_s > 3$ k Ω . The only exception is when gain error is important.

Figure 40 illustrates the 10 Hz noise. As expected, the results are between the previous two figures.

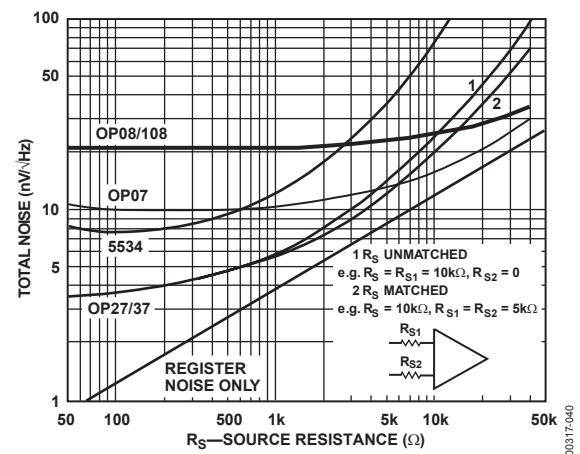


Figure 40. 10 Hz Noise vs. Source Resistance (Includes Resistor Noise) Audio Applications

For reference, typical source resistances of some signal sources are listed in Table 7.

Table 7.

Device	Source Impedance	Comments
Strain Gauge	<500 Ω	Typically used in low frequency applications.
Magnetic Tape Head	<1500 Ω	Low is very important to reduce self-magnetization problems when direct coupling is used. OP27 I_B can be neglected.
Magnetic Phonograph Cartridges	<1500 Ω	Similar need for low I_B in direct coupled applications. OP27 does not introduce any self-magnetization problems.
Linear Variable Differential Transformer	<1500 Ω	Used in rugged servo-feedback applications. Bandwidth of interest is 400 Hz to 5 kHz.

Table 8. Open-Loop Gain

Frequency	OP07	OP27	OP37
At 3 Hz	100 dB	124 dB	125 dB
At 10 Hz	100 dB	120 dB	125 dB
At 30 Hz	90 dB	110 dB	124 dB

AUDIO APPLICATIONS

Figure 41 is an example of a phono pre-amplifier circuit using the **OP27** for A1; R1-R2-C1-C2 form a very accurate RIAA network with standard component values. The popular method to accomplish RIAA phono equalization is to employ frequency dependent feedback around a high quality gain block. Properly chosen, an RC network can provide the three necessary time constants of 3180 μ s, 318 μ s, and 75 μ s.

For initial equalization accuracy and stability, precision metal film resistors and film capacitors of polystyrene or polypropylene are recommended because they have low voltage coefficients, dissipation factors, and dielectric absorption. (High-k ceramic capacitors should be avoided here, though low-k ceramics, such as NPO types that have excellent dissipation factors and somewhat lower dielectric absorption, can be considered for small values.)

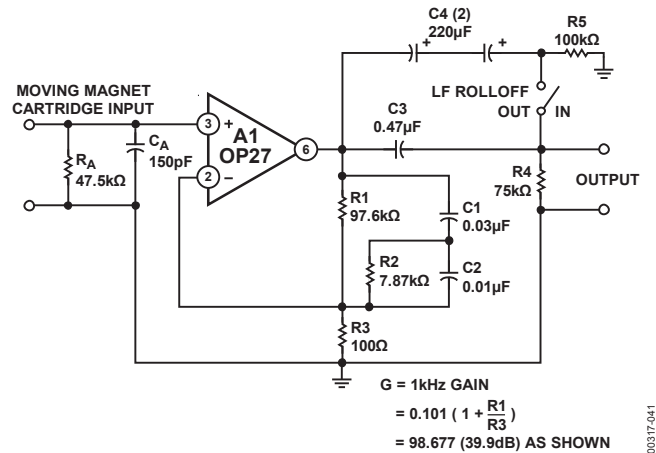


Figure 41. Phono Preamplifier Circuit

The **OP27** brings a 3.2 nV/ $\sqrt{\text{Hz}}$ voltage noise and 0.45 pA/ $\sqrt{\text{Hz}}$ current noise to this circuit. To minimize noise from other sources, R3 is set to a value of 100 Ω , generating a voltage noise of 1.3 nV/ $\sqrt{\text{Hz}}$. The noise increases the 3.2 nV/ $\sqrt{\text{Hz}}$ of the amplifier by only 0.7 dB. With a 1 k Ω source, the circuit noise measures 63 dB below a 1 mV reference level, unweighted, in a 20 kHz noise bandwidth.

Gain (G) of the circuit at 1 kHz can be calculated by the expression:

$$G = 0.101 \left(1 + \frac{R1}{R3} \right)$$

For the values shown, the gain is just under 100 (or 40 dB). Lower gains can be accommodated by increasing R3, but gains higher than 40 dB show more equalization errors because of the 8 MHz gain bandwidth of the **OP27**.

This circuit is capable of very low distortion over its entire range, generally below 0.01% at levels up to 7 V rms. At 3 V output levels, it produces less than 0.03% total harmonic distortion at frequencies up to 20 kHz.

Capacitor C3 and Resistor R4 form a simple -6 dB per octave rumble filter, with a corner at 22 Hz. As an option, the switch selected Shunt Capacitor C4, a nonpolarized electrolytic, bypasses the low frequency roll-off. Placing the rumble filter's high-pass action after the preamplifier has the desirable result of discriminating against the RIAA-amplified low frequency noise components and pickup produced low frequency disturbances.

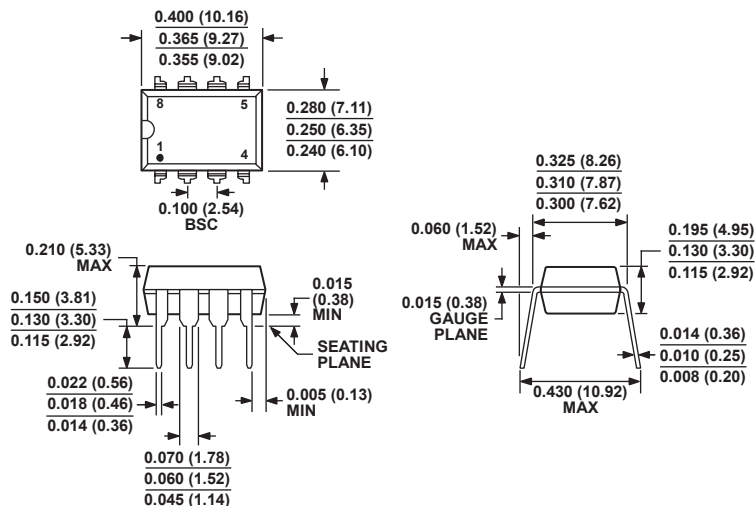
A preamplifier for NAB tape playback is similar to an RIAA phono preamplifier, though more gain is typically demanded, along with equalization requiring a heavy low frequency boost. The circuit in Figure 41 can be readily modified for tape use, as shown by Figure 42.

A 150 Ω resistor and R1 and R2 gain resistors connected to a noiseless amplifier generate 220 nV of noise in a 20 kHz bandwidth, or 73 dB below a 1 mV reference level. Any practical amplifier can only approach this noise level; it can never exceed it. With the OP27 and T1 specified, the additional noise degradation is close to 3.6 dB (or -69.5 referenced to 1 mV).

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OUTLINE DIMENSIONS

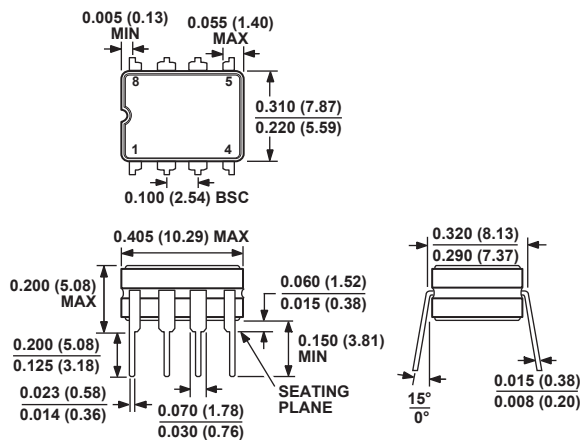


COMPLIANT TO JEDEC STANDARDS MS-001
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.

Figure 46. 8-Lead Plastic Dual-in-Line Package [PDIP]
(N-8)

P-Suffix

Dimensions shown in inches and (millimeters)



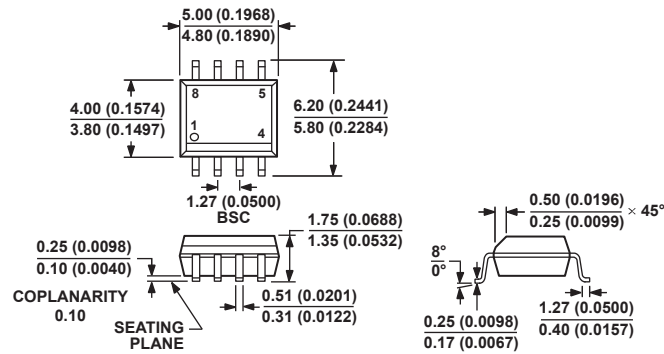
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 47. 8-Lead Ceramic DIP – Glass Hermetic Seal [CERDIP]

(Q-8)

Z-Suffix

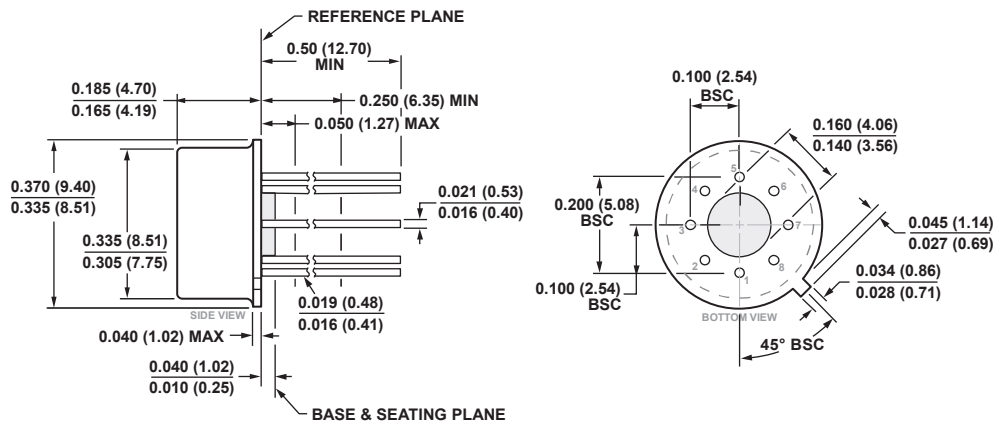
Dimensions shown in inches and (millimeters)



COMPLIANT TO JEDEC STANDARDS MS-012-AA
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(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 48. 8-Lead Standard Small Outline Package [SOIC_N]
Narrow Body
(R-8)
S-Suffix
Dimensions shown in millimeters and (inches)

012407-A



COMPLIANT TO JEDEC STANDARDS MO-002-AK
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 49. 8-Lead Metal Can [TO-99]
(H-08)
J-Suffix
Dimensions shown in inches and (millimeters)

01-15-2015-B

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
OP27AJ/883C	–55°C to +125°C	8-Lead Metal Can (TO-99)	J-Suffix (H-08)
OP27GJZ	–40°C to +85°C	8-Lead Metal Can (TO-99)	J-Suffix (H-08)
OP27AZ	–55°C to +125°C	8-Lead CERDIP	Z-Suffix (Q-8)
OP27AZ/883C	–55°C to +125°C	8-Lead CERDIP	Z-Suffix (Q-8)
OP27EZ	–25°C to +85°C	8-Lead CERDIP	Z-Suffix (Q-8)
OP27GZ	–40°C to +85°C	8-Lead CERDIP	Z-Suffix (Q-8)
OP27EPZ	0°C to +70°C	8-Lead PDIP	P-Suffix (N-8)
OP27GPZ	–40°C to +85°C	8-Lead PDIP	P-Suffix (N-8)
OP27GS	–40°C to +85°C	8-Lead SOIC_N	S-Suffix (R-8)
OP27GS-REEL7	–40°C to +85°C	8-Lead SOIC_N	S-Suffix (R-8)
OP27GSZ	–40°C to +85°C	8-Lead SOIC_N	S-Suffix (R-8)
OP27GSZ-REEL	–40°C to +85°C	8-Lead SOIC_N	S-Suffix (R-8)
OP27GSZ-REEL7	–40°C to +85°C	8-Lead SOIC_N	S-Suffix (R-8)
OP27NBC		Die	

¹ The OP27GJZ, OP27EPZ, OP27GPZ, OP27GSZ, OP27GSZ-REEL, and OP27GSZ-REEL7 are RoHS compliant parts.